



SN65HVD25x 面向高数据传输速率大型网络的 Turbo CAN 收发器，支持功能安全特性

1 特性

- 符合 ISO11898-2 标准的要求
- Turbo CAN:
 - 短时和对称传播延迟时间以及针对增强型时序裕量的快速环路时间
 - CAN 网络中更快的数据速率
- I/O 电压范围支持 3.3V 和 5V MCU
- 未上电时的理想无源特性
 - 总线和逻辑引脚处于高阻态（无负载）
 - 上电和掉电时总线上无毛刺脉冲
- 保护特性
 - 人体模型 (HBM) 静电放电 (ESD) 保护超过 $\pm 12\text{kV}$
 - 总线故障保护 -27V 至 40V
 - 电源引脚上的欠压保护
 - 驱动器主计时功能 (TXD DTO)
 - SN65HVD257: 接收器主导超时 (RXD DTO)
 - SN65HVD257: 故障输出引脚
 - 热关断保护
- 运行温度范围 -40°C 至 125°C

2 应用

- 采用 TXD DTO 将高负载 CAN 网络中的 1Mbps 速率降至 10kbps
- 工业自动化、控制、传感器和驱动系统
- 楼宇、安全和温度控制自动化
- 电信基站状态和控制
- SN65HVD257: 为冗余和多拓扑 CAN 网络提供功能安全特性
- CAN 总线标准，例如 CANopen、DeviceNet、NMEA2000、ARINC825、ISO11783 和 CANaerospace

3 说明

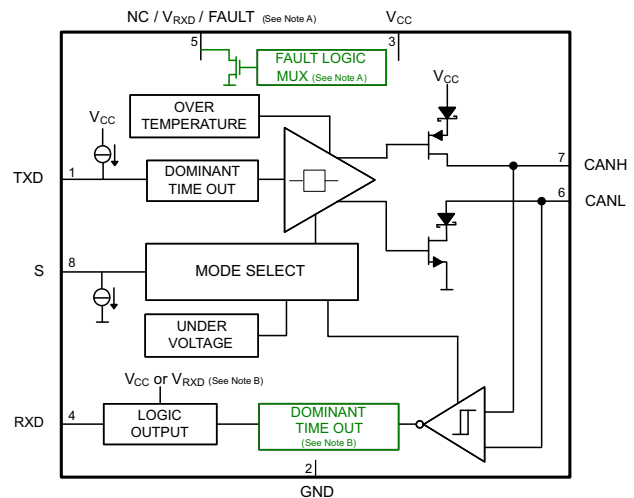
这款 CAN 收发器符合 ISO1189-2 高速 CAN（控制器局域网）物理层标准。其在小型 CAN 网络中的数据传输速率高达 1Mbps 以上，并且在大型高负载网络中具有更高的时序余裕和数据传输速率。此器件提供多种保护特性来提高器件和 CAN 网络的耐用性。SN65HVD257 器件新增了一些特性，以便能够轻松设计具有故障指示的冗余和多拓扑网络，从而使 CAN 系统获得更高级别的功能安全特性。

器件信息⁽¹⁾

器件型号	封装	封装尺寸（标称值）
SN65HVD255 SN65HVD256 SN65HVD257	SOIC (8)	4.90mm x 3.91mm

(1) 要了解所有可用封装，请见数据表末尾的可订购产品附录。

框图



- 引脚 5 的功能取决于器件：在 SN65HVD255 器件中为 NC；在 SN65HVD256 器件中为 RXD 输出电平转换器件的 V_{RXD} ；而在 SN65HVD257 器件中为故障输出。
- RXD 逻辑输出在仅 5V 供电器件（SN65HVD255 和 SN65HVD257）中被驱动为 5V V_{CC} ；而在输出电平转换器件中（SN65HVD256）被驱动为 V_{RXD} 。
- RXD（接收器）主导状态超时选项与器件相关，仅在 SN65HVD257 器件上提供。



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4 修订历史记录

Changes from Revision C (September 2013) to Revision D Page

- 已添加 引脚配置和功能部分, ESD 额定值表, 开关特性表, 典型特性部分, 特性描述部分, 器件功能模式, 应用和实
施部分, 电源相关建议部分, 布局部分, 器件和文档支持部分, 以及机械、封装和可订购信息部分 1

Changes from Revision B (June 2012) to Revision C Page

- Added [Table 1](#), Receiver Differential Input Voltage Threshold Test 12
- Added [Figure 13](#), Example Timing Diagram for TXD DTO and FAULT Pin 17
- Added Bus Loading, Length, and Number of Nodes subsection 22

Changes from Revision A (June 2012) to Revision B Page

- Added SN65HVD257 status to production in Ordering Information table 4

Changes from Original (December 2011) to Revision A Page

- 已更新特性列表 1
- 已更新应用列表 1
- 已添加 内容至说明部分 1
- 已更新框图 - 功能方框图以包含 HVD257 和注释更改。 1
- Changed the DEVICE OPTIONS table 4
- Added SN65HVD257 to the D PACKAGE OPTIONS images 4
- Added SN65HVD257 FAULT pin to the PIN FUNCTIONS table 4
- Added SN65HVD257 to the Ordering Information table 4
- Added SN65HVD257 FAULT pin information to the Abs Max table 5
- Added FAULT pin information to the ROC table 6
- changed R_{ID} - Differential input resistance value from 3 k Ω to 30 k Ω 8
- Added t_{RXD_DTO} - SN65HVD257 information 10

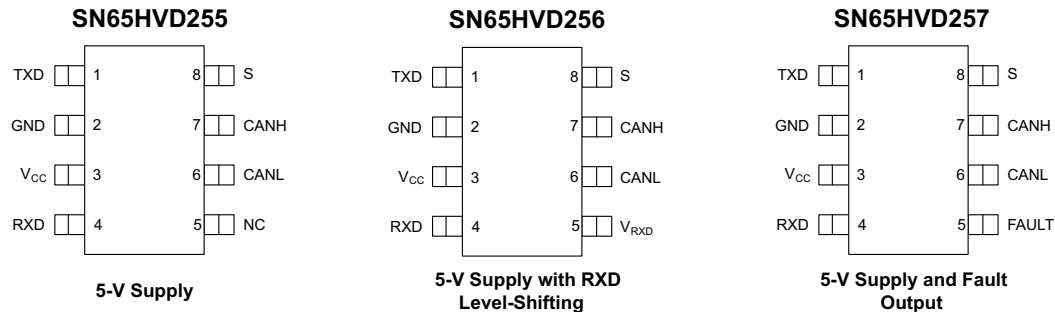
• Added Figure 4 , <i>RXD Dominant Timeout Test Circuit and Measurement</i>	11
• Added Figure 5 , <i>FAULT Test and Measurement</i>	11
• Added RXD Dominant Timeout (SN65HVD257) section.....	15
• Added FAULT pin information	16
• Added footnote for SN65HVD257 function to Table 5	19
• Added 5-V V_{CC} with FAULT Open-Drain Output Device (SN65HVD257) section.....	21
• Added <i>Example: Functional Safety Using the SN65HVD257 in a Redundant Physical Layer CAN Network Topology</i> section	24

5 Device Options

PART NUMBER	I/O SUPPLY for RXD	TXD DTO	RXD DTO	FAULT Output	COMMENT
SN65HVD255	No	Yes	No	No	'251 and '1050 functional upgrade with Turbo CAN fast loop times and TXD DTO protection allowing data rates down to 10 kbps
SN65HVD256	Yes	Yes	No	No	'251 and '1050 functional upgrade with Turbo CAN fast loop times and TXD DTO protection allowing data rates down to 10 kbps. RXD output level shifting through RXD supply input.
SN65HVD257	No	Yes	Yes	Yes	'251 and '1050 functional upgrade with Turbo CAN fast loop times, TXD and RXD DTO protection allowing data rates down to 10 kbps and fault output pin

6 Pin Configuration and Functions

**D Package
8-Pin SOIC
(Top View)**



Pin Functions

PIN		TYPE	DESCRIPTION
NAME	NO.		
TXD	1	I	CAN transmit data input (LOW for dominant and HIGH for recessive bus states)
GND	2	GND	Ground connection
V _{CC}	3	Supply	Transceiver 5-V supply voltage
RXD	4	O	CAN receive data output (LOW for dominant and HIGH for recessive bus states)
NC	5	NC	SN65HVD255: No Connect
V _{RXD}		Supply	SN65HVD256: RXD output supply voltage
FAULT		O	SN65HVD257: Open drain FAULT output pin
CANL	6	I/O	Low level CAN bus line
CANH	7	I/O	High level CAN bus line
S	8	I	Mode select: S (silent mode) select pin (active high)

7 Specifications

7.1 Absolute Maximum Ratings⁽¹⁾⁽²⁾

			MIN	MAX	UNIT
V _{CC}	Supply voltage		−0.3	6.1	V
V _{RXD}	RXD Output supply voltage	SN65HVD256	−0.3	6 and V _{RXD} ≤ V _{CC} + 0.3	V
V _{BUS}	CAN Bus I/O voltage (CANH, CANL)		−27	40	V
V _{Logic_Input}	Logic input pin voltage (TXD, S)		−0.3	6	V
V _{Logic_Output}	Logic output pin voltage (RXD)	SN65HVD255, SN65HVD257	−0.3	6	V
V _{Logic_Output}	Logic output pin voltage (RXD)	SN65HVD256	−0.3	6 and V _I ≤ V _{RXD} + 0.3	V
I _{O(RXD)}	RXD (Receiver) output current			12	mA
I _{O(FAULT)}	FAULT output current	SN65HVD257		20	mA
T _J	Operating virtual junction temperature (see Power Dissipation)		−40	150	°C
T _A	Ambient temperature (see Power Dissipation)		−40	125	°C

- (1) Stresses beyond those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under *Recommended Operating Conditions*. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
- (2) All voltage values, except differential I/O bus voltages, are with respect to ground terminal.

7.2 ESD Ratings

				VALUE	UNIT
V _(ESD)	Electrostatic discharge	Human body model (HBM), per ANSI/ESDA/JEDEC JS-001 ⁽¹⁾	All pins	±2500	V
			CAN bus pins (CANH, CANL) ⁽²⁾	±12000	
		Charged-device model (CDM), per JEDEC specification JESD22-C101 ⁽³⁾	All pins	±750	
			Machine model	±250	
		IEC 61400-4-2 according to GIFT-ICT CAN EMC test spec ⁽⁴⁾	CAN bus pins (CANH, CANL) to GND	±8000	
		ISO7637 Transients according to GIFT - ICT CAN EMC test spec ⁽⁵⁾	CAN bus pins (CANH, CANL)	Pulse 1	−100
				Pulse 2	+75
				Pulse 3a	−150
				Pulse 3b	+100

- (1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.
- (2) Test method based upon JEDEC Standard 22 Test Method A114, CAN bus pins stressed with respect to GND.
- (3) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.
- (4) IEC 61000-4-2 is a system level ESD test. Results given here are specific to the GIFT-ICT CAN EMC Test specification conditions. Different system level configurations may lead to different results.
- (5) ISO7637 is a system level transient test. Results given here are specific to the GIFT-ICT CAN EMC Test specification conditions. Different system level configurations may lead to different results.

SN65HVD255, SN65HVD256, SN65HVD257

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7.3 Recommended Operating Conditions

		MIN	MAX	UNIT
V _{CC}	Supply voltage	4.5	5.5	V
V _{RXD}	RXD supply (SN65HVD256 only)	2.8	5.5	
V _I or V _{IC}	CAN bus terminal voltage (separately or common mode)	–2	7	
V _{ID}	CAN bus differential voltage	–6	6	
V _{IH}	Logic HIGH level input (TXD, S)	2	5.5	
V _{IL}	Logic LOW level input (TXD, S)	0	0.8	
I _{OH} (DRVR)	CAN BUS Driver High level output current	–70		mA
I _{OL} (DRVR)	CAN BUS Driver Low level output current		70	
I _{OH} (RXD)	RXD pin HIGH level output current	–2		
I _{OL} (RXD)	RXD pin LOW level output current		2	
I _O (FAULT)	FAULT pin LOW level output current		2	
T _A	Operational free-air temperature (see Power Dissipation)	–40	125	°C

7.4 Thermal Information

THERMAL METRIC ⁽¹⁾		SN65HVD25x	UNIT
		D (SOIC)	
		8 PINS	
R _{θJA}	Junction-to-ambient thermal resistance, High-K thermal resistance ⁽²⁾	107.5	°C/W
R _{θJC(top)}	Junction-to-case (top) thermal resistance	56.7	°C/W
R _{θJB}	Junction-to-board thermal resistance	48.9	°C/W
ψ _{JT}	Junction-to-top characterization parameter	12.1	°C/W
ψ _{JB}	Junction-to-board characterization parameter	48.2	°C/W

(1) For more information about traditional and new thermal metrics, see the *IC Package Thermal Metrics* application report, [SPRA953](#).

(2) The junction-to-ambient thermal resistance under natural convection is obtained in a simulation on a JEDEC-standard, High-K board, as specified in JESD51-7, in an environment described in JESD51-2a.

7.5 Electrical Characteristics

Over recommended operating conditions, $T_A = -40^{\circ}\text{C}$ to 125°C (unless otherwise noted). SN65HVD256 device $V_{\text{RXD}} = V_{\text{CC}}$.

PARAMETER		TEST CONDITIONS		MIN	TYP ⁽¹⁾	MAX	UNIT
SUPPLY CHARACTERISTICS							
I _{CC}	5-V Supply current	Normal Mode (Driving Dominant)	See Figure 6, TXD = 0 V, R _L = 50 Ω, C _L = open, R _{CM} = open, S = 0 V		60	85	mA
		Normal Mode (Driving Dominant – bus fault)	See Figure 6, TXD = 0 V, S = 0 V, CANH = −12 V, R _L = open, C _L = open, R _{CM} = open		130	180	
		Normal Mode (Driving Dominant)	See Figure 6, TXD = 0 V, R _L = open (no load), C _L = open, R _{CM} = open, S = 0 V		10	20	
		Normal Mode (Recessive)	See Figure 6, TXD = V _{CC} , R _L = 50 Ω, C _L = open, R _{CM} = open, S = 0 V		10	20	
		Silent Mode	See Figure 6, TXD = V _{CC} , R _L = 50 Ω, C _L = open, R _{CM} = open, S = V _{CC}		2.5	5	
I _{RXD}	RXD Supply current (SN65HVD256 only)	All modes	RXD Floating, TXD = 0 V			500	μA
UV _{VCC}	Undervoltage detection on V _{CC} for protected mode			3.5		4.45	V
V _{HYS(UVCC)}	Hysteresis voltage on UV _{VCC}				200		mV
UV _{RXD}	Undervoltage detection on V _{RXD} for protected mode (SN65HVD256 only)			1.3		2.75	V
V _{HYS(UVRXD)}	Hysteresis voltage on UV _{RXD} (SN65HVD256 only)				80		mV
S PIN (MODE SELECT INPUT)							
V _{IH}	HIGH-level input voltage			2			V
V _{IL}	LOW-level input voltage					0.8	V
I _{IH}	HIGH-level input leakage current		S = V _{CC} = 5.5 V	7		100	μA
I _{IL}	Low-level input leakage current		S = 0 V, V _{CC} = 5.5 V	−1	0	1	μA
I _{LKG(OFF)}	Unpowered leakage current		S = 5.5 V, V _{CC} = 0 V, V _{RXD} = 0 V	7	35	100	μA
TXD PIN (CAN TRANSMIT DATA INPUT)							
V _{IH}	HIGH level input voltage			2			V
V _{IL}	LOW level input voltage					0.8	V
I _{IH}	HIGH level input leakage current		TXD = V _{CC} = 5.5 V	−2.5	0	1	μA
I _{IL}	Low level input leakage current		TXD = 0 V, V _{CC} = 5.5 V	−100	−25	−7	μA
I _{LKG(OFF)}	Unpowered leakage current		TXD = 5.5 V, V _{CC} = 0 V, V _{RXD} = 0 V	−1	0	1	μA
C _I	Input Capacitance				3.5		pF
RXD PIN (CAN RECEIVE DATA OUTPUT)							
V _{OH}	HIGH level output voltage		See Figure 7, I _O = −2 mA. For devices with V _{RXD} supply V _{OH} = 0.8 × V _{RXD}	0.8 × V _{CC}			V
V _{OL}	LOW level output voltage		See Figure 7, I _O = 2 mA			0.4	V
I _{LKG(OFF)}	Unpowered leakage current		RXD = 5.5 V, V _{CC} = 0 V, V _{RXD} = 0 V	−1	0	1	μA

(1) All typical values are at 25°C and supply voltages of $V_{\text{CC}} = 5\ \text{V}$ and $V_{\text{RXD}} = 5\ \text{V}$, $R_L = 60\ \Omega$.

Electrical Characteristics (continued)

Over recommended operating conditions, $T_A = -40^{\circ}\text{C}$ to 125°C (unless otherwise noted). SN65HVD256 device $V_{\text{RXD}} = V_{\text{CC}}$.

PARAMETER			TEST CONDITIONS	MIN	TYP ⁽¹⁾	MAX	UNIT
DRIVER ELECTRICAL CHARACTERISTICS							
V _{O(D)}	Bus output voltage (dominant)	CANH	See Figure 15 and Figure 6, TXD = 0 V, S = 0 V, R _L = 60 Ω, C _L = open, R _{CM} = open	2.75		4.5	V
		CANL		0.5		2.25	
V _{O(R)}	Bus output voltage (recessive)		See Figure 15 and Figure 6, TXD = V _{CC} , V _{RXD} = V _{CC} , S = V _{CC} or 0 V ⁽²⁾ , R _L = open (no load), R _{CM} = open	2	0.5 × V _{CC}	3	V
V _{OD(D)}	Differential output voltage (dominant)		See Figure 15 and Figure 6, TXD = 0 V, S = 0 V, 45 Ω ≤ R _L ≤ 65 Ω, C _L = open, R _{CM} = 330 Ω, −2 V ≤ V _{CM} ≤ 7 V, 4.75 V ≤ V _{CC} ≤ 5.25 V	1.5		3	V
			See Figure 15 and Figure 6, TXD = 0 V, S = 0 V, 45 Ω ≤ R _L ≤ 65 Ω, C _L = open, R _{CM} = 330 Ω, −2 V ≤ V _{CM} ≤ 7 V, 4.5 V ≤ V _{CC} ≤ 5.5 V	1.25		3.2	
V _{OD(R)}	Differential output voltage (recessive)		See Figure 15 and Figure 6, TXD = V _{CC} , S = 0 V, R _L = 60 Ω, C _L = open, R _{CM} = open	−0.12		0.012	V
			See Figure 15 and Figure 6, TXD = V _{CC} , S = 0 V, R _L = open (no load), C _L = open, R _{CM} = open, −40°C ≤ T _A ≤ 85°C	−0.100		0.050	
V _{SYM}	Output symmetry (dominant or recessive) (V _{CC} − V _{O(CANH)} − V _{O(CANL)})		See Figure 15 and Figure 6, S at 0 V, R _L = 60 Ω, C _L = open, R _{CM} = open	−0.4		0.4	V
I _{OS(SS)_DOM}	Short circuit steady-state output current, Dominant		See Figure 15 and Figure 11, V _{CANH} = 0 V, CANL = open, TXD = 0 V	−160			mA
			See Figure 15 and Figure 11, V _{CANL} = 32 V, CANH = open, TXD = 0 V			160	
I _{OS(SS)_REC}	Short circuit steady-state output current, Recessive		See Figure 15 and Figure 11, −20 V ≤ V _{BUS} ≤ 32 V, Where V _{BUS} = CANH = CANL, TXD = V _{CC} , Normal and Silent Modes	−8		8	mA
C _O	Output capacitance		See Input capacitance to ground (C _I) in the following Receiver Electrical Characteristics section of this table				
RECEIVER ELECTRICAL CHARACTERISTICS							
V _{IT+}	Positive-going input threshold voltage, normal mode		See Figure 7, Table 5 and Table 1			900	mV
V _{IT−}	Negative-going input threshold voltage, normal mode			500			mV
V _{HYS}	Hysteresis voltage (V _{IT+} - V _{IT−})					125	mV
I _{IOFF(LKG)}	Power-off (unpowered) bus input leakage current		V _{CANH} = V _{CANL} = 5 V, V _{CC} = 0 V, V _{RXD} = 0 V			5.5	μA
C _I	Input capacitance to ground (CANH or CANL)		TXD = V _{CC} , V _{RXD} = V _{CC} , V _I = 0.4 sin (4E6 π t) + 2.5 V			25	pF
C _{ID}	Differential input capacitance		TXD = V _{CC} , V _{RXD} = V _{CC} , V _I = 0.4 sin (4E6 π t)			10	pF
R _{ID}	Differential input resistance		TXD = V _{CC} = V _{RXD} = 5 V, S = 0 V	30		80	kΩ
R _{IN}	Input resistance (CANH or CANL)			15		40	kΩ
R _{IN(M)}	Input resistance matching: [1 − R _{IN(CANH)} / R _{IN(CANL)}] × 100%		V _(CANH) = V _(CANL) , −40°C ≤ T _A ≤ 85°C	−3%		3%	

(2) For the bus output voltage (recessive) will be the same if the device is in normal mode with S pin LOW or if the device is in silent mode with the S pin HIGH.

Electrical Characteristics (continued)

Over recommended operating conditions, $T_A = -40^{\circ}\text{C}$ to 125°C (unless otherwise noted). SN65HVD256 device $V_{\text{RXD}} = V_{\text{CC}}$.

PARAMETER	TEST CONDITIONS	MIN	TYP ⁽¹⁾	MAX	UNIT
FAULT PIN (FAULT OUTPUT), SN65HVD257 ONLY					
I_{CH}	Output current high level FAULT = V_{CC} , see Figure 5	-10		10	μA
I_{CL}	Output current low level FAULT = 0.4 V, see Figure 5	5	12		mA

7.6 Power Dissipation

THERMAL METRIC	TEST CONDITIONS	TYP	UNIT
P_D Average power dissipation	$V_{\text{CC}} = 5\text{ V}$, $V_{\text{RXD}} = 5\text{ V}$, $T_J = 27^{\circ}\text{C}$, $R_L = 60\ \Omega$, S at 0 V, Input to TXD at 250 kHz, 25% duty cycle square wave, $C_{L_RXD} = 15\text{ pF}$. Typical CAN operating conditions at 500 kbps with 25% transmission (dominant) rate.	115	mW
	$V_{\text{CC}} = 5.5\text{ V}$, $V_{\text{RXD}} = 5.5\text{ V}$, $T_J = 150^{\circ}\text{C}$, $R_L = 50\ \Omega$, S at 0 V, Input to TXD at 500 kHz, 50% duty cycle square wave, $C_{L_RXD} = 15\text{ pF}$. Typical high load CAN operating conditions at 1 Mbps with 50% transmission (dominant) rate and loaded network.	268	
Thermal shutdown temperature		170	$^{\circ}\text{C}$
Thermal shutdown hysteresis		5	$^{\circ}\text{C}$

7.7 Switching Characteristics

over operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
DEVICE SWITCHING CHARACTERISTICS					
$t_{\text{PROP(LOOP1)}}$	Total loop delay, driver input (TXD) to receiver output (RXD), recessive to dominant See Figure 9, S = 0 V, $R_L = 60\ \Omega$, $C_L = 100\text{ pF}$, $C_{L_RXD} = 15\text{ pF}$			150	ns
$t_{\text{PROP(LOOP2)}}$	Total loop delay, driver input (TXD) to receiver output (RXD), dominant to recessive			150	
I_{MODE}	Mode change time, from Normal to Silent or from Silent to Normal See Figure 8			20	μS
DRIVER SWITCHING CHARACTERISTICS					
t_{pHR}	Propagation delay time, HIGH TXD to Driver Recessive		50	70	ns
t_{pLD}	Propagation delay time, LOW TXD to Driver Dominant		40	70	
$t_{\text{sk(p)}}$	Pulse skew ($ t_{\text{pHR}} - t_{\text{pLD}} $)		10		
t_{R}	Differential output signal rise time		10	30	
t_{F}	Differential output signal fall time		17	30	
$t_{\text{R(10k)}}$	Differential output signal rise time, $R_L = 10\text{ k}\Omega$			35	ns
$t_{\text{F(10k)}}$	Differential output signal fall time, $R_L = 10\text{ k}\Omega$			100	
$t_{\text{TXD_DTO}}$	Dominant timeout ⁽¹⁾ See Figure 10, $R_L = 60\ \Omega$, $C_L = \text{open}$	1175		3700	μs

- (1) The TXD dominant timeout ($t_{\text{TXD_DTO}}$) disables the driver of the transceiver when the TXD has been dominant longer than $t_{\text{TXD_DTO}}$, which releases the bus lines to recessive, thus preventing a local failure from locking the bus dominant. The driver may only transmit dominant again after TXD has been returned HIGH (recessive). While this protects the bus from local faults locking the bus dominant, it limits the minimum data rate possible. The CAN protocol allows a maximum of eleven successive dominant bits (on TXD) for the worst case, where five successive dominant bits are followed immediately by an error frame. This, along with the $t_{\text{TXD_DTO}}$ minimum, limits the minimum bit rate. The minimum bit rate may be calculated by: Minimum Bit Rate = $11 / t_{\text{TXD_DTO}} = 11\text{ bits} / 1175\ \mu\text{s} = 9.4\text{ kbps}$.

Switching Characteristics (continued)

over operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
RECEIVER SWITCHING CHARACTERISTICS						
t_{pRH}	Propagation delay time, recessive input to high output	See Figure 7, $C_{L_RXD} = 15$ pF		70	90	ns
t_{pDL}	Propagation delay time, dominant input to low output			70	90	ns
t_R	Output signal rise time			4	20	ns
t_F	Output signal fall time			4	20	ns
$t_{RXD_DTO}^{(2)}$	Receiver dominant time out (SN65HVD257 only) See Figure 4, $C_{L_RXD} = 15$ pF		1380		4200	μ s

- (2) The RXD timeout (t_{RXD_DTO}) disables the RXD output in the case that the bus has been dominant longer than t_{RXD_DTO} , which releases RXD pin to the recessive state (high), thus preventing a dominant bus failure from permanently keeping the RXD pin low. The RXD pin will automatically resume normal operation once the bus has been returned to a recessive state. While this protects the protocol controller from a permanent dominant state, it limits the minimum data rate possible. The CAN protocol allows a maximum of eleven successive dominant bits (on RXD) for the worst case, where five successive dominant bits are followed immediately by an error frame. This, along with the t_{RXD_DTO} minimum, limits the minimum bit rate. The minimum bit rate may be calculated by: Minimum Bit Rate = $11 / t_{RXD_DTO} = 11 \text{ bits} / 1380 \mu\text{s} = 8 \text{ kbps}$.

7.8 Typical Characteristics

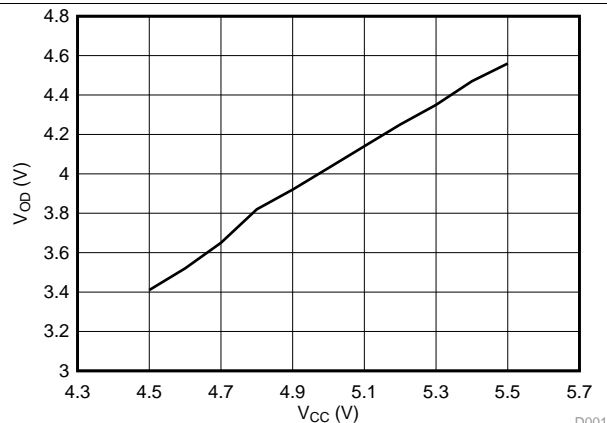


Figure 1. Differential Output Voltage vs Supply Voltage

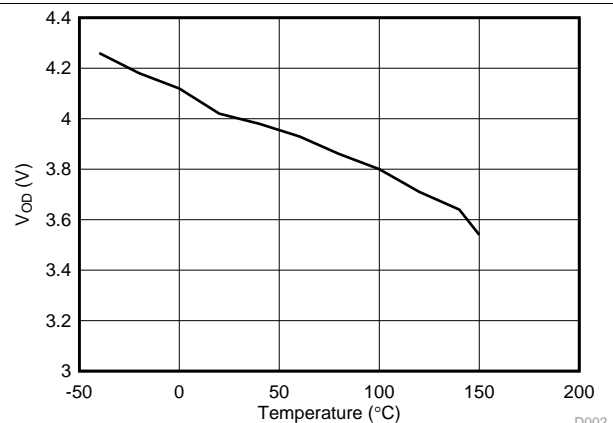


Figure 2. Differential Output Voltage vs Ambient Temperature

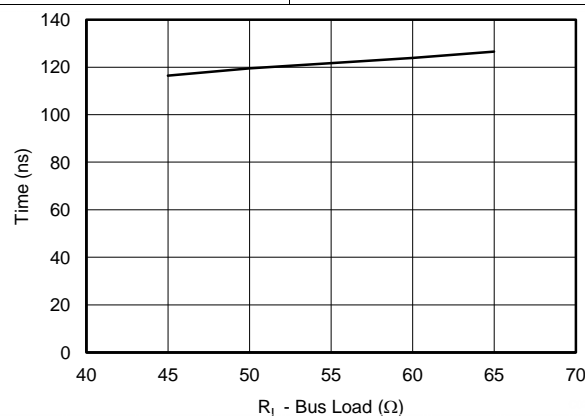


Figure 3. Typical Transceiver Loop Delay vs Bus Loading

8 Parameter Measurement Information

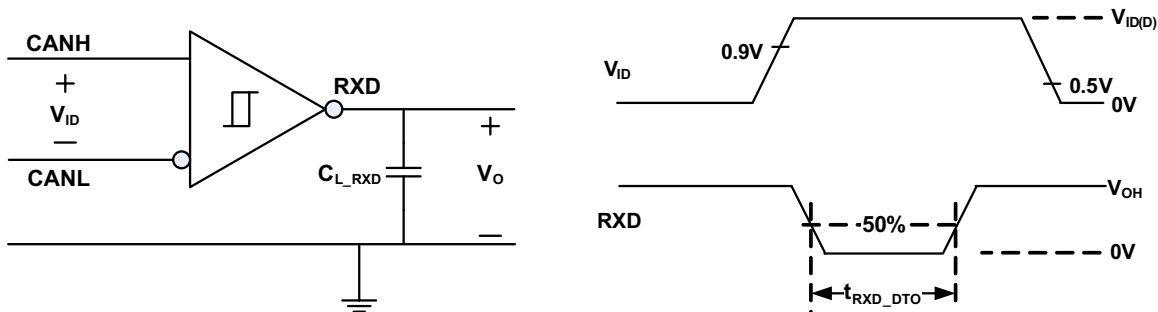


Figure 4. RXD Dominant Timeout Test Circuit and Measurement

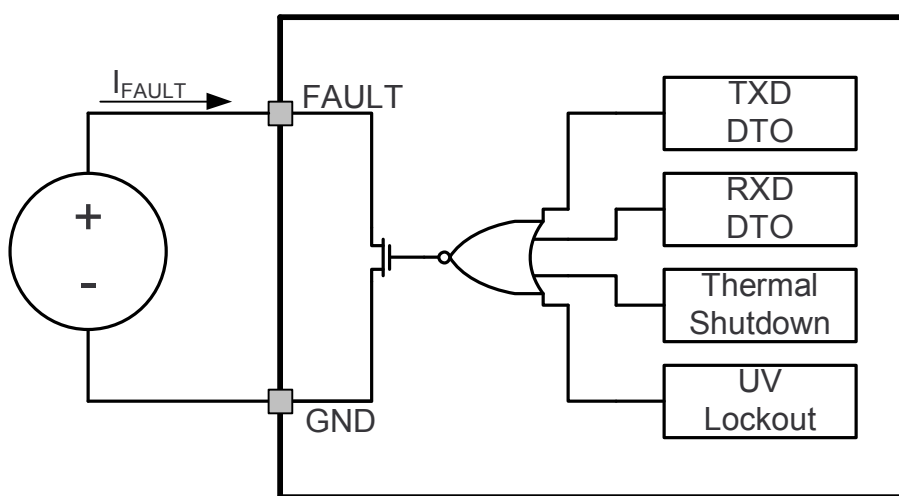


Figure 5. FAULT Test and Measurement

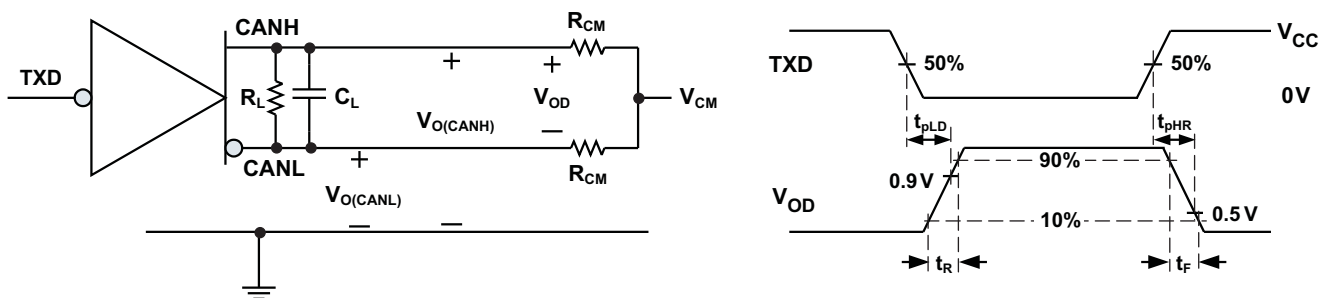
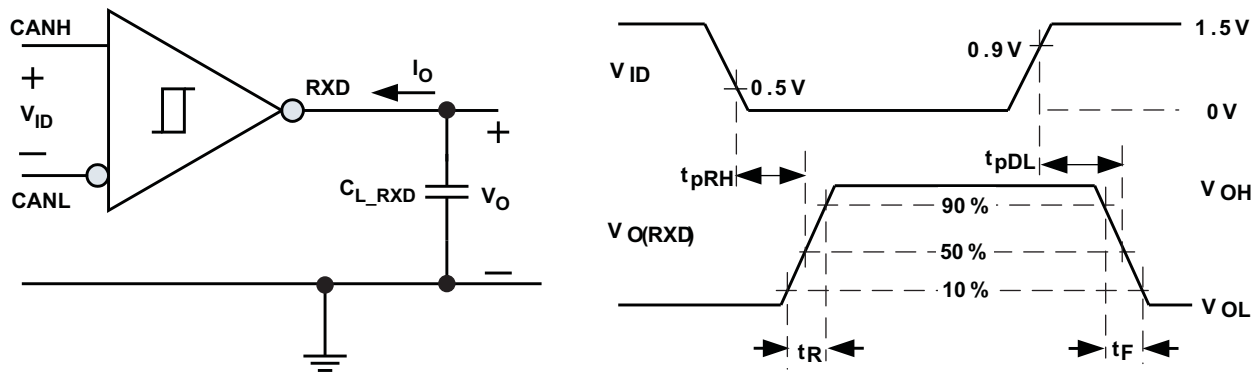
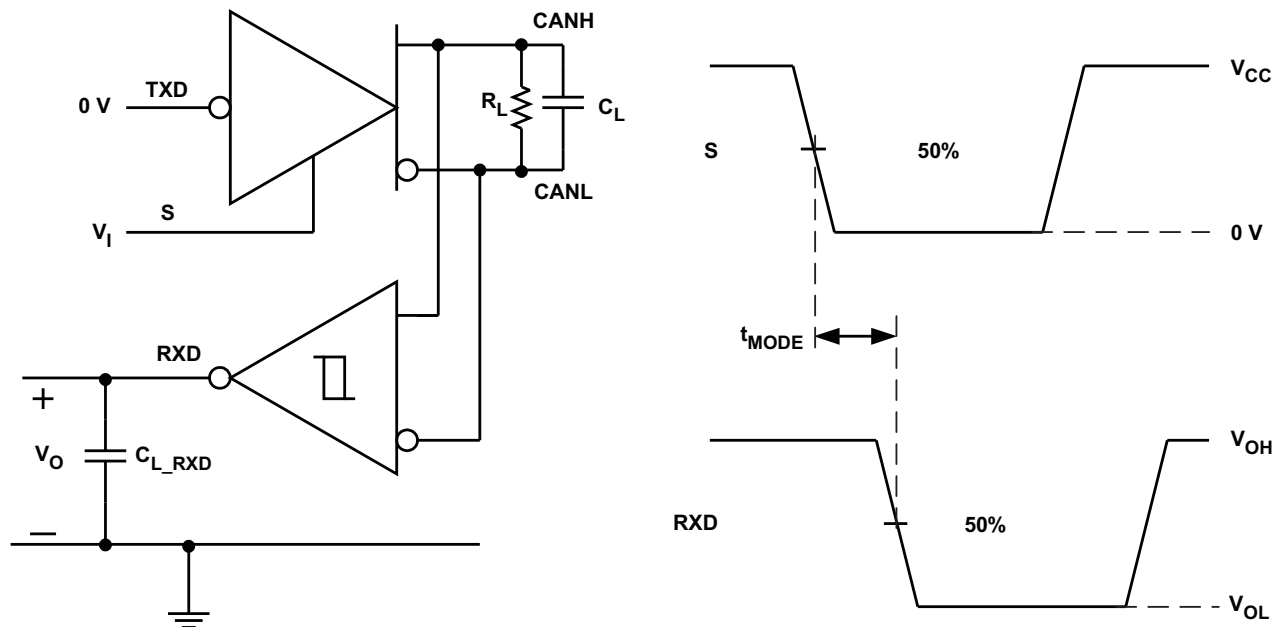


Figure 6. Driver Test Circuit and Measurement

Parameter Measurement Information (continued)

Figure 7. Receiver Test Circuit and Measurement

Figure 8. t_{MODE} Test Circuit and Measurement
Table 1. Receiver Differential Input Voltage Threshold Test

INPUT			OUTPUT	
V_{CANH}	V_{CANL}	$ V_{ID} $	R_{XD}	
-1.1 V	-2.0 V	900 mV	L	V_{OL}
7.0 V	6.1 V	900 mV	L	
-1.5 V	-2.0 V	500 mV	H	V_{OH}
7.0 V	6.5 V	500 mV	H	
Open	Open	X	H	

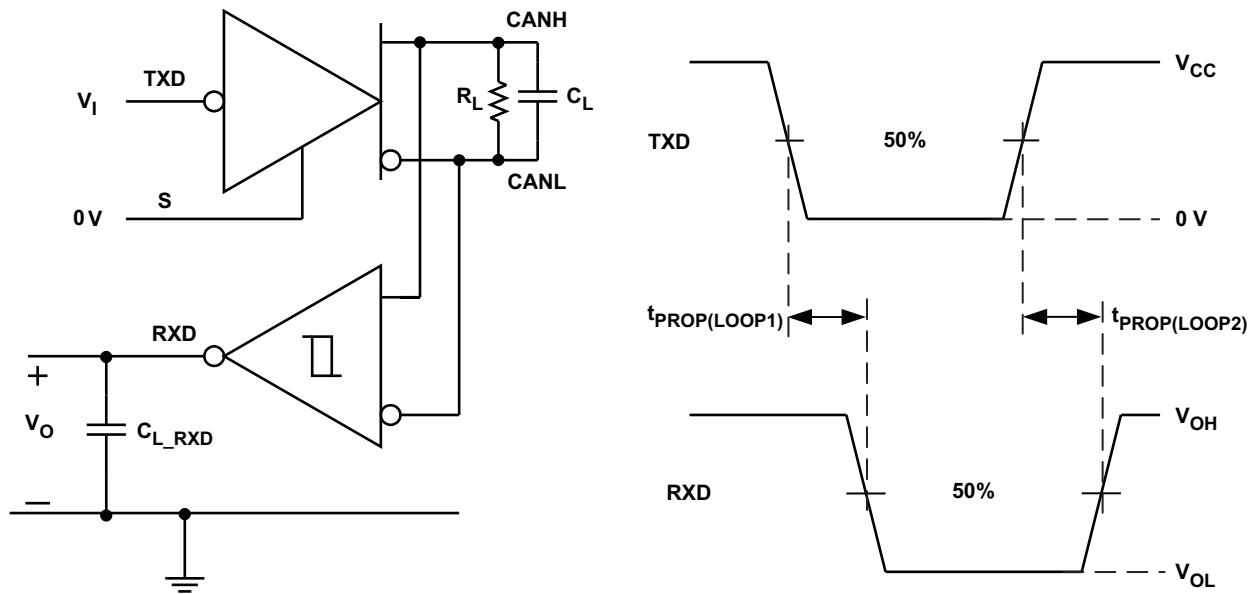


Figure 9. $T_{PROP(LOOP)}$ Test Circuit and Measurement

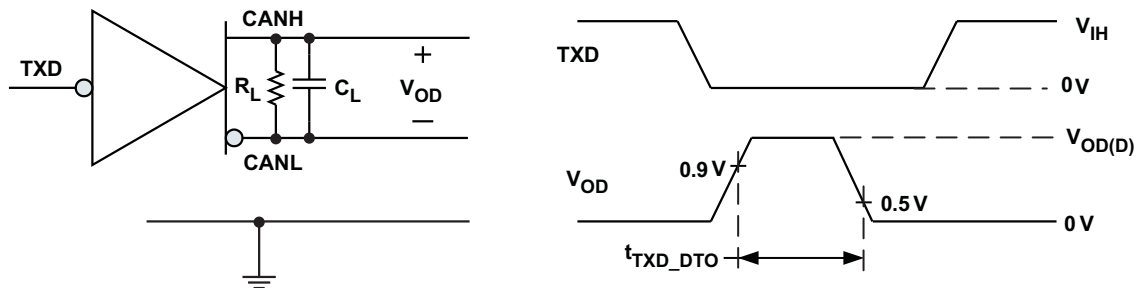


Figure 10. TXD Dominant Timeout Test Circuit and Measurement

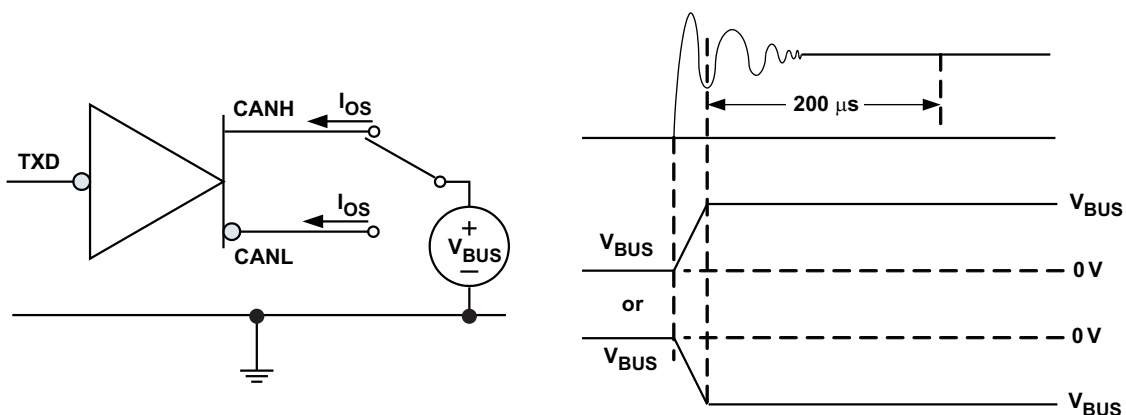


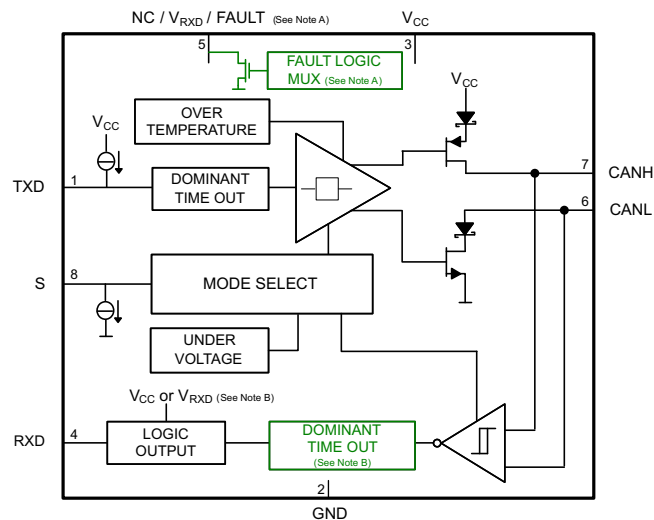
Figure 11. Driver Short Circuit Current Test and Measurement

9 Detailed Description

9.1 Overview

The SN65HVD25x family of bus transceiver devices are compatible with the ISO 11898-2 High Speed CAN (Controller Area Network) physical layer standard. The SN65HVD25x devices are designed to interface between the differential bus lines and the CAN protocol controller at data rates up to 1 Mbps (megabits per second).

9.2 Functional Block Diagram



- Pin 5 function is device dependent; NC on SN65HVD255, V_{RXD} for RXD output level-shifting device on the SN65HVD256 device, and FAULT Output on the SN65HVD257 device.
- RXD logic output is driven to 5-V V_{CC} on 5-V only supply devices (SN65HVD255, SN65HVD257) and driven to V_{RXD} on output level-shifting device (SN65HVD256).
- RXD (Receiver) Dominant State Time Out is a device dependent option available only on the SN65HVD257 device.

9.3 Feature Description

9.3.1 TXD Dominant Timeout (DTO)

During normal mode (the only mode where the CAN driver is active), the TXD DTO circuit prevents the transceiver from blocking network communication in the event of a hardware or software failure where TXD is held dominant longer than the timeout period t_{TXD_DTO} . The DTO circuit timer starts on a falling edge on TXD. The DTO circuit disables the CAN bus driver if no rising edge is seen before the timeout period expires, which frees the bus for communication between other nodes on the network. The CAN driver is reactivated when a recessive signal is seen on TXD pin, thus clearing the TXD DTO condition. The receiver and RXD pin still reflect the CAN bus, and the bus pins are biased to recessive level during a TXD dominant timeout.

NOTE

The minimum dominant TXD time allowed by the TXD DTO circuit limits the minimum possible transmitted data rate of the device. The CAN protocol allows a maximum of eleven successive dominant bits (on TXD) for the worst case, where five successive dominant bits are followed immediately by an error frame. This, along with the t_{TXD_DTO} minimum, limits the minimum data rate. Calculate the minimum transmitted data rate by: Minimum Data Rate = $11 / t_{TXD_DTO}$.

Feature Description (continued)

9.3.2 RXD Dominant Timeout (SN65HVD257)

The SN65HVD257 device has a RXD dominant timeout (RXD DTO) circuit that prevents a bus stuck dominant fault from permanently driving the RXD output dominant (low) when the bus is held dominant longer than the timeout period t_{RXD_DTO} . The RXD DTO timer starts on a falling edge on RXD (bus going dominant). If no rising edge (bus returning recessive) is seen before the timeout constant of the circuit expires (t_{RXD_DTO}), the RXD pin returns high (recessive). The RXD output is reactivated to mirror the bus receiver output when a recessive signal is seen on the bus, clearing the RXD dominant timeout. The CAN bus pins are biased to the recessive level during a RXD DTO.

NOTE

The minimum dominant RXD time allowed by the RXD DTO limits the minimum possible received data rate of the device. The CAN protocol allows a maximum of eleven successive dominant bits for the worst case transmission, where five successive dominant bits are followed immediately by an error frame. This, along with the t_{RXD_DTO} minimum, limits the minimum data rate. The minimum received data rate may be calculated by:
Minimum Data Rate = $11 / t_{RXD_DTO}$.

9.3.3 Thermal Shutdown

If the junction temperature of the device exceeds the thermal shut down threshold, the device turns off the CAN driver circuits thus blocking the TXD to bus transmission path. The shutdown condition is cleared when the junction temperature drops below the thermal shutdown temperature of the device.

NOTE

During thermal shutdown the CAN bus drivers turn off; thus, no transmission is possible from TXD to the bus. The CAN bus pins are biased to recessive level during a thermal shutdown, and the receiver to RXD path remains operational.

9.3.4 Undervoltage Lockout

The supply pins have undervoltage detection that places the device in protected mode, which protects the bus during an undervoltage event on either the V_{CC} or V_{RXD} supply pins.

Table 2. Undervoltage Lockout 5-V Only Devices (SN65HVD255 and SN65HVD257)

V_{CC}	DEVICE STATE	BUS OUTPUT	RXD
GOOD	Normal	Per Device State and TXD	Mirrors Bus
BAD	Protected	High Impedance	High Impedance (3-state)

Table 3. Undervoltage Lockout 5 V and V_{RXD} Device (SN65HVD256)

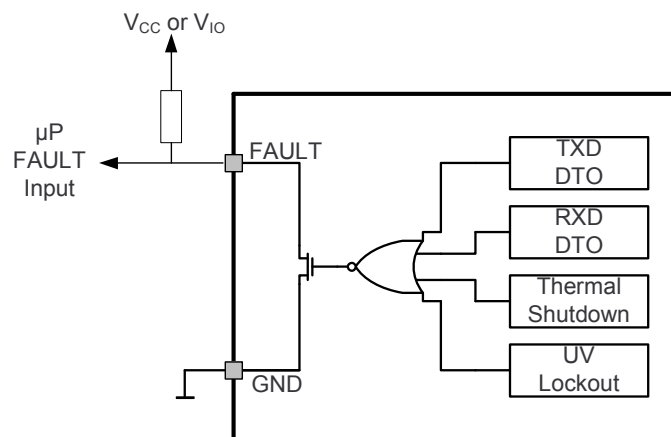
V_{CC}	V_{RXD}	DEVICE STATE	BUS OUTPUT	RXD
GOOD	GOOD	Normal	Per Device State and TXD	Mirrors Bus
BAD	GOOD	Protected	High Impedance	High (Recessive)
GOOD	BAD	Protected	Recessive	High Impedance (3-state)
BAD	BAD	Protected	High Impedance	High Impedance (3-state)

NOTE

After an undervoltage condition is cleared and the supplies have returned to valid levels, the device typically resumes normal operation in 300 μ s.

9.3.5 FAULT Pin (SN65HVD257)

If one or more of the faults (TXD dominant timeout, RXD dominant timeout, thermal shutdown or undervoltage lockout) occurs, the FAULT pin (open-drain) turns off, resulting in a high level when externally pulled up to V_{CC} or I/O supply.


Figure 12. FAULT Pin Function Diagram and Application

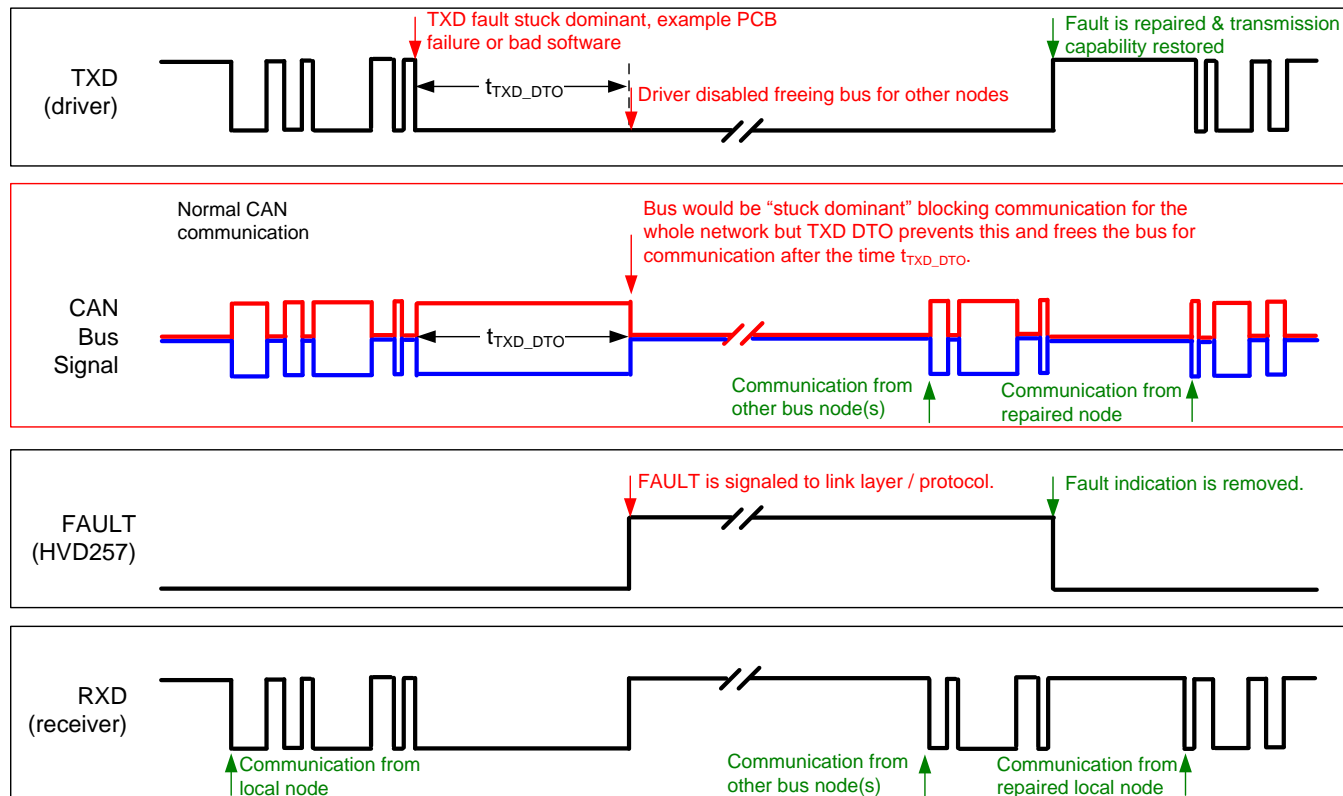


Figure 13. Example Timing Diagram for TXD DTO and FAULT Pin

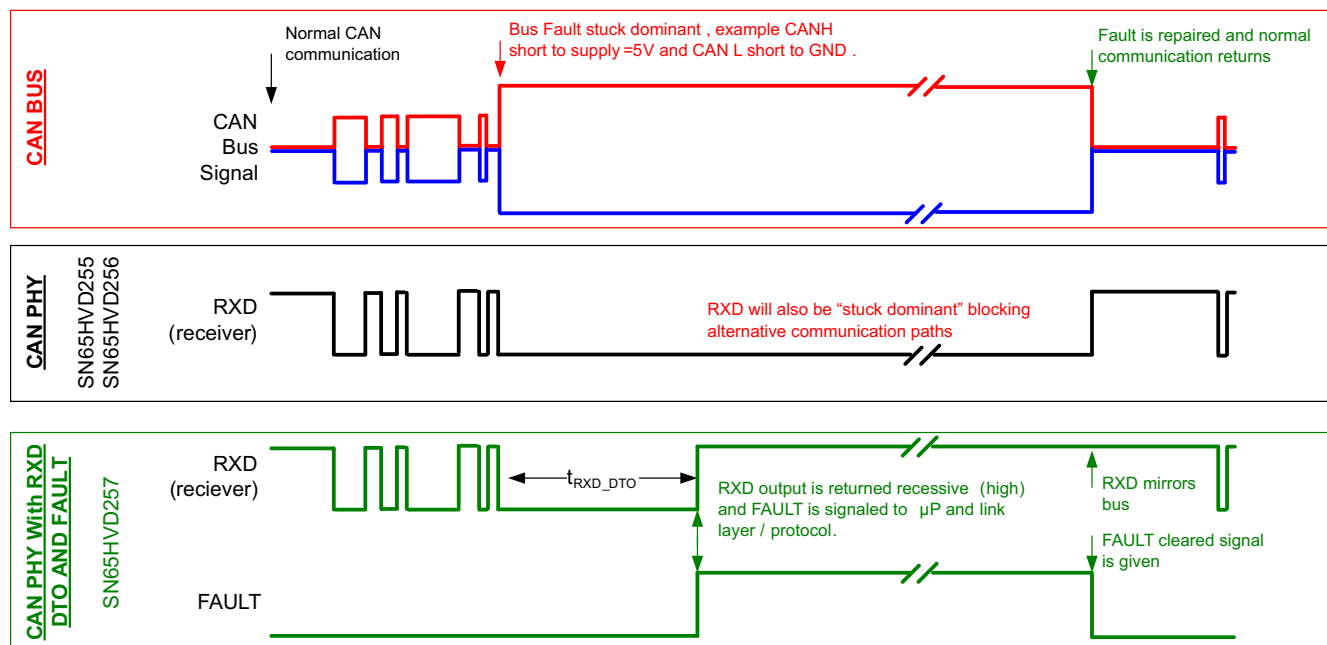


Figure 14. Example Timing Diagram for Devices With and Without RXD DTO and FAULT Pin

9.3.6 Unpowered Device

The SN65HVD25x device is designed to be an *ideal passive* or *no load* to the CAN bus if it is unpowered. The bus pins (CANH, CANL) have extremely low leakage currents when the device is unpowered, so they will not load down the bus. This is critical if some nodes of the network will be unpowered while the rest of the network remains in operation. The logic pins also have extremely low leakage currents when the device is unpowered to avoid loading down other circuits that may remain powered.

9.3.7 Floating Pins

The device has internal pullups and pulldowns on critical pins to place the device into known states if the pins float. The TXD pin is pulled up to V_{CC} to force a recessive input level if the pin floats. The S pin is pulled down to GND to force the device into normal mode if the pin floats.

9.3.8 CAN Bus Short-Circuit Current Limiting

The SN65HVD25x device has several protection features that limit the short circuit current when a CAN bus line is shorted. These features include driver current limiting (dominant and recessive). The device has TXD dominant state time out to prevent permanent higher short circuit current of the dominant state during a system fault. During CAN communication, the bus switches between dominant and recessive states with the data and control fields bits; thus the short circuit current may be viewed either as the instantaneous current during each bus state or as a DC average current. For system current (power supply) and power considerations in the termination resistors and common-mode choke ratings, use the average short circuit current. Determine the ratio of dominant and recessive bits by the data in the CAN frame plus the following factors of the protocol and PHY that force either recessive or dominant at the following times:

- Control fields with set bits
- Bit stuffing
- Interframe space
- TXD dominant time out (fault case limiting)

These factors ensure a minimum recessive amount of time on the bus even if the data field contains a high percentage of dominant bits.

The short circuit current of the bus depends on the ratio of recessive to dominant bits and their respective short circuit currents. The average short circuit current may be calculated with [Equation 1](#).

$$I_{OS(AVG)} = \%Transmit \times [(\%REC_Bits \times I_{OS(SS_REC)}) + (\%DOM_Bits \times I_{OS(SS_DOM)})] + [\%Receive \times I_{OS(SS_REC)}] \quad (1)$$

where:

$I_{OS(AVG)}$ is the average short circuit current

%Transmit is the percentage the node is transmitting CAN messages

%Receive is the percentage the node is receiving CAN messages

%REC_Bits is the percentage of recessive bits in the transmitted CAN messages

%DOM_Bits is the percentage of dominant bits in the transmitted CAN messages

$I_{OS(SS_REC)}$ is the recessive steady state short circuit current

$I_{OS(SS_DOM)}$ is the dominant steady state short circuit current

NOTE

Consider the short circuit current and possible fault cases of the network when sizing the power ratings of the termination resistance and other network components.

9.4 Device Functional Modes

Table 4. Driver Function Table

DEVICE	INPUTS		OUTPUTS		DRIVEN BUS STATE
	S ⁽¹⁾⁽²⁾	TXD ⁽¹⁾⁽³⁾	CANH ⁽¹⁾	CANL ⁽¹⁾	
All Devices	L or Open	L	H	L	Dominant
		H or Open	Z	Z	Recessive
	H	X	Z	Z	Recessive

(1) H = high level, L = low level, X = irrelevant, Z = common mode (recessive) bias to $V_{CC} / 2$. See [Figure 15](#) and [Figure 16](#) for bus state and common mode bias information.

(2) Devices have an internal pulldown to GND on S pin. If S pin is open the pin will be pulled low and the device will be in normal mode.

(3) Devices have an internal pullup to V_{CC} on TXD pin. If the TXD pin is open the pin will be pulled high and the transmitter will remain in recessive (nondriven) state.

Table 5. Receiver Function Table

DEVICE MODE	CAN DIFFERENTIAL INPUTS $V_{ID} = V_{CANH} - V_{CANL}$	BUS STATE	RXD PIN ⁽¹⁾
Normal or Silent	$V_{ID} \geq 0.9 \text{ V}$	Dominant	L ⁽²⁾
	$0.5 \text{ V} < V_{ID} < 0.9 \text{ V}$?	?
	$V_{ID} \leq 0.5 \text{ V}$	Recessive	H
	Open ($V_{ID} \approx 0 \text{ V}$)	Open	H

(1) H = high level, L = low level, ? = indeterminate.

(2) RXD output remains dominant (low) as long as the bus is dominant. On the SN65HVD257 device with RXD dominant timeout, when the bus has been dominant longer than the dominant timeout, t_{RXD_DTO} , the RXD pin will return recessive (high). See [RXD Dominant Timeout \(SN65HVD257\)](#) for a description of behavior during receiving a bus stuck dominant condition.

9.4.1 Operating Modes

The device has two main operating modes: normal mode and silent mode. Operating mode selection is made via the S input pin.

Table 6. Operating Modes

S Pin	MODE	DRIVER	RECEIVER	RXD PIN
LOW	Normal Mode	Enabled (ON)	Enabled (ON)	Mirrors Bus State ⁽¹⁾
HIGH	Silent Mode	Disabled (OFF)	Enabled (ON)	Mirrors Bus State

(1) Mirrors bus state: low if CAN bus is dominant, high if CAN bus is recessive.

9.4.2 Can Bus States

The CAN bus has two states during powered operation of the device: *dominant* and *recessive*. A dominant bus state is when the bus is driven differentially, corresponding to a logic low on the TXD and RXD pin. A recessive bus state is when the bus is biased to $V_{CC} / 2$ via the high-resistance internal input resistors R_{IN} of the receiver, corresponding to a logic high on the TXD and RXD pins. See Figure 15 and Figure 16.

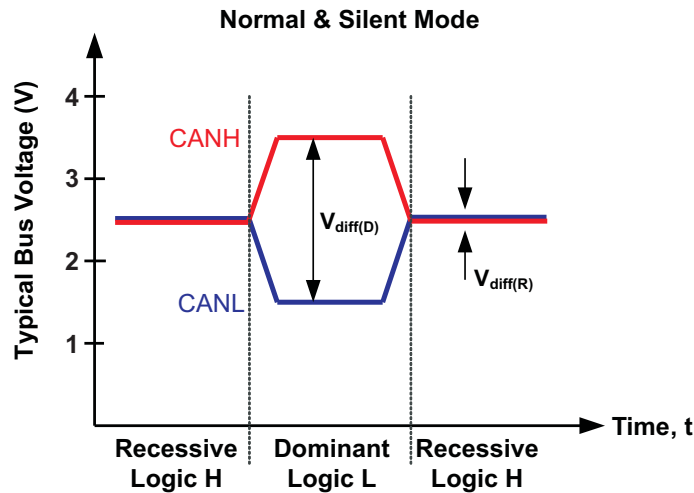


Figure 15. Bus States (Physical Bit Representation)

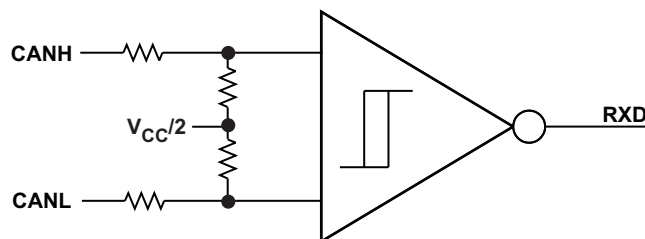


Figure 16. Simplified Recessive Common Mode Bias and Receiver

9.4.3 Normal Mode

Select the normal mode of device operation by setting S low. The CAN driver and receiver are fully operational and CAN communication is bidirectional. The driver is translating a digital input on TXD to a differential output on CANH and CANL. The receiver is translating the differential signal from CANH and CANL to a digital output on RXD.

9.4.4 Silent Mode

Activate silent mode (receive only) by setting S high. The CAN driver is turned off while the receiver remains active and RXD outputs the received bus state.

NOTE

Silent mode may be used to implement babbling idiot protection, to ensure that the driver does not disrupt the network during a local fault. Silent mode may also be used in redundant systems to select or de-select the redundant transceiver (driver) when needed.

9.4.5 Digital Inputs and Outputs

9.4.5.1 5-V V_{CC} Only Devices (SN65HVD255 and SN65HVD257)

The 5-V V_{CC} device is supplied by a single 5-V rail. The digital inputs are 5-V and 3.3-V compatible. The SN65HVD255 and SN65HVD257 devices have a 5-V (V_{CC}) level RXD output. TXD is internally pulled up to V_{CC} and S is internally pulled down to GND.

NOTE

TXD is internally pulled up to V_{CC} and the S pin is internally pulled down to GND. However, the internal bias may only put the device into a known state if the pins float. The internal bias may be inadequate for system-level biasing. TXD pullup strength and CAN bit timing require special consideration when the SN65HVD25x devices are used with an open-drain TXD output on the CAN controller. An adequate external pullup resistor must be used to ensure that the CAN controller output of the μP maintains adequate bit timing input to the SN65HVD25x devices.

9.4.5.2 5-V V_{CC} With V_{RXD} RXD Output Supply Devices (SN65HVD256)

This device is a 5-V V_{CC} CAN transceiver with a separate supply for the RXD output, V_{RXD} . The digital inputs are 5-V and 3.3-V compatible. The SN65HVD256 device has a V_{RXD} level RXD output. TXD remains weakly pulled up to V_{CC} .

NOTE

On device versions with a V_{RXD} supply that shifts the RXD output level, the input pins of the device remain the same. TXD remains weakly pulled up to V_{CC} internally. Thus, a small I_{IH} current flows if the TXD input is used below V_{CC} levels.

9.4.5.3 5-V V_{CC} with FAULT Open-Drain Output Device (SN65HVD257)

The SN65HVD257 device has a FAULT output pin (open-drain). FAULT must be pulled up to V_{CC} or I/O supply level through an external resistor.

NOTE

Because the FAULT output pin is open-drain, it actively pulls down when there is no fault and becomes high-impedance when a fault condition is detected. An external pullup resistor to the V_{CC} or I/O supply of the system must be used to pull the pin high to indicate a fault to the host microprocessor. The open-drain architecture makes the fault pin compatible with 3.3-V and 5-V I/O-level systems. The pullup current, selected by the pullup resistance value, must be as low as possible while achieving the desired voltage level output in the system with margin against noise.

10 Application and Implementation

NOTE

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

10.1 Application Information

10.1.1 Bus Loading, Length, and Number of Nodes

The ISO 11898 standard states that a CAN bus should have a maximum of 30 nodes, be less than 40 meters from end to end, and should have no stubs greater than 0.3 meters. However, with careful design, users can have longer cables, longer stub lengths, and many more nodes to a bus. A large number of nodes requires a transceiver with high input impedance, such as the SN65HVD25x family devices.

Many CAN organizations and standards have scaled the use of CAN for applications outside the original ISO11898 standard. They have made system level trade-offs for data rate, cable length, and parasitic loading of the bus. Examples of some of these specifications are: ARINC825, CANopen, DeviceNet, and NMEA200.

A CAN network design is a series of trade-offs, but these devices operate over wide common-mode range. In ISO11898-2, the driver differential output is specified with a 60- Ω load (the two 120- Ω termination resistors in parallel) and the differential output must be greater than 1.5 V. The SN65HVD25x devices are specified to meet the 1.5-V requirement with a 45- Ω load incorporating the worst case including parallel transceivers. The differential input resistance of the SN65HVD25x devices is a minimum of 30 K Ω . If 167 SN65HVD25x family transceivers are in parallel on a bus, this is equivalent to a 180- Ω differential load worst case. That transceiver load of 180 Ω in parallel with the 60 Ω gives a total 45 Ω . Therefore, the SN65HVD25x family theoretically supports over 167 transceivers on a single bus segment with margin to the 1.2-V minimum differential input at each node. However, CAN network design margin must be given for signal loss across the system and cabling, parasitic loadings, network imbalances, ground offsets, and signal integrity; thus a practical maximum number of nodes is typically much lower. Bus length may also be extended beyond the original ISO11898 standard of 40 m by careful system design and data-rate tradeoffs. For example, CAN open network design guidelines allow the network to be up to 1 km with changes in the termination resistance, cabling, less than 64 nodes, and a significantly lowered data rate.

This flexibility in CAN network design is one of the key strengths of the various extensions and additional standards that have been built on the original ISO11898 CAN standard. In using this flexibility comes the responsibility of good network design and balancing these tradeoffs.

10.2 Typical Applications

10.2.1 Typical 5-V Microcontroller Application

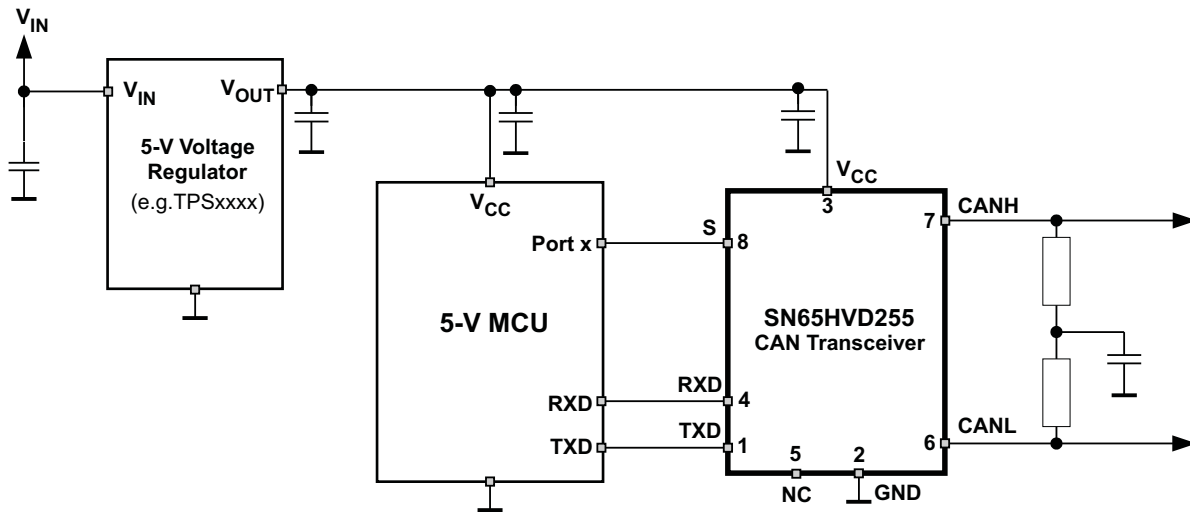


Figure 17. Typical 5-V Application

10.2.1.1 Design Requirements

10.2.1.1.1 CAN Termination

The ISO11898 standard specifies the interconnect to be a twisted-pair cable (shielded or unshielded) with 120-Ω characteristic impedance (Z_0). Resistors equal to the characteristic impedance of the line must be used to terminate both ends of the cable to prevent signal reflections. Unterminated drop lines (stubs) connecting nodes to the bus must be kept as short as possible to minimize signal reflections. The termination may be on the cable or in a node, but if nodes may be removed from the bus, the termination must be carefully placed so that it is not removed from the bus.

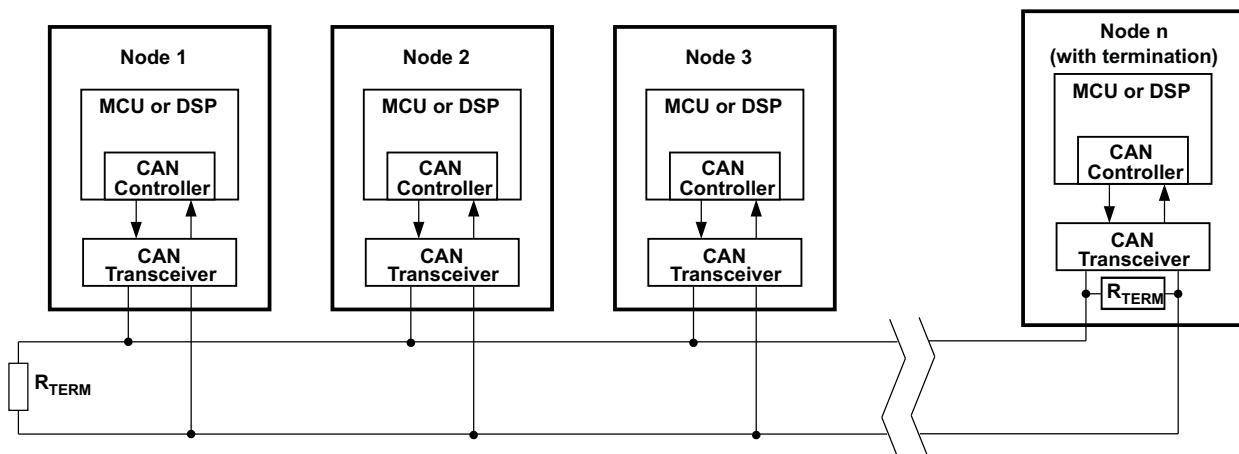


Figure 18. Typical CAN Bus

Termination may be a single 120-Ω resistor at the end of the bus either on the cable or in a terminating node. If filtering and stabilization of the common mode voltage of the bus is desired, then split termination may be used (see Figure 19). Split termination improves the electromagnetic emissions behavior of the network by eliminating fluctuations in the bus common-mode voltages at the start and end of message transmissions.

Typical Applications (continued)

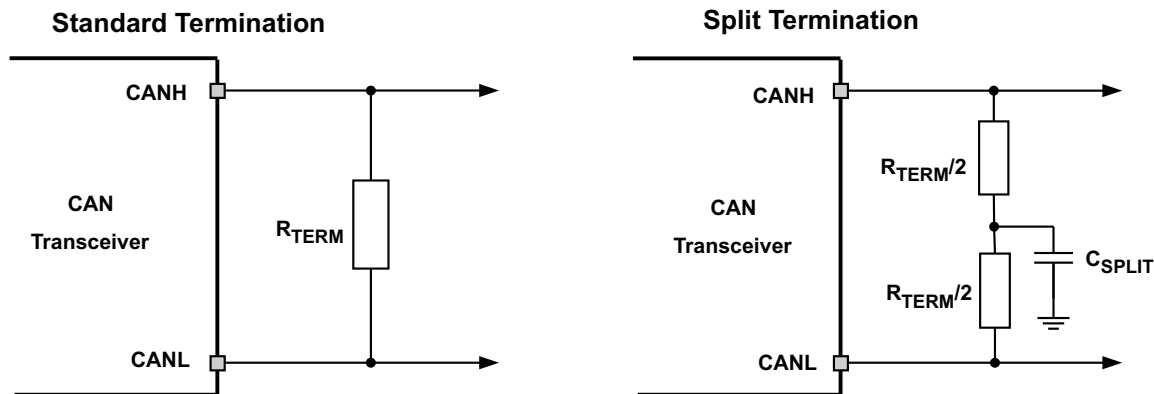


Figure 19. CAN Bus Termination Concepts

10.2.1.2 Detailed Design Procedure

10.2.1.2.1 Example: Functional Safety Using the SN65HVD257 in a Redundant Physical Layer CAN Network Topology

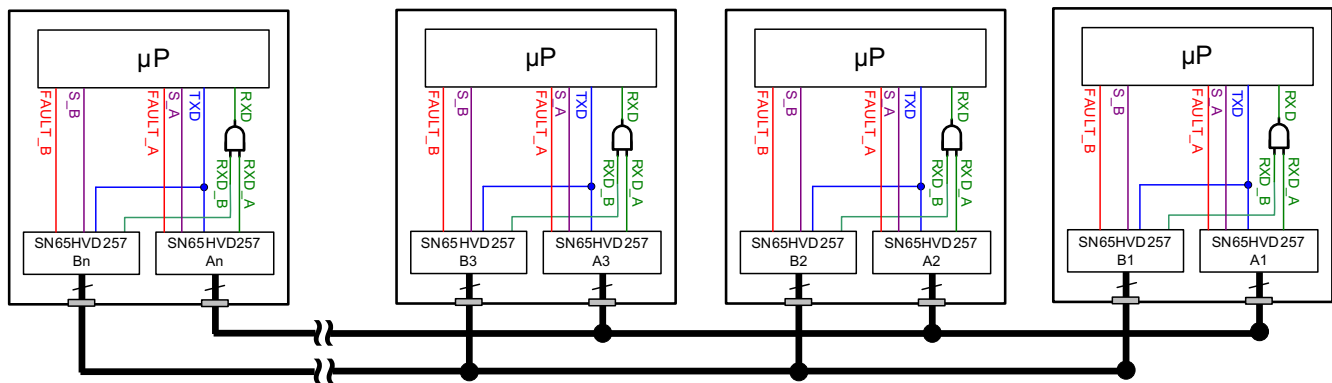
CAN is a standard linear bus topology using 120-Ω twisted-pair cabling. The SN65HVD257 CAN device includes several features to use the CAN physical layer in nonstandard topologies with only one CAN link layer controller (μP) interface. This allows much greater flexibility in the physical topology of the bus while reducing the digital controller and software costs. The combination of RXD DTO and the FAULT output allows great flexibility, control, and monitoring of these applications.

A simple example of this flexibility is to use two SN65HVD257 devices in parallel with an AND gate to achieve redundancy (parallel) of the physical layer (cabling and PHYs) in a CAN network.

For the CAN bit-wise arbitration to work, the RXD outputs of the transceivers must connect through AND gate logic so that a dominant bit (low) from any of the branches is received by the link layer logic (μP) and appears to the link layer and above as a single physical network. The RXD DTO feature prevents a bus stuck dominant fault in a single branch from taking down the entire network by forcing the RXD pin for the transceivers on the branch with the fault back to the recessive after the t_{RXD_DTO} time. The remaining branch of the network continues to function. The FAULT pin of the transceivers on the branch with the fault indicates this through the FAULT output to their host processors, which diagnose the failure condition. The S pin (silent mode pin) may be used to put a branch in silent mode to check each branch for other faults. Therefore, it is possible to implement a robust and redundant CAN network topology in a very simple and low-cost manner.

These concepts can be expanded into more complicated and flexible CAN network topologies to solve various system-level challenges with a networked infrastructure.

Typical Applications (continued)



- A. CAN nodes with termination are PHY A, PHY B, PHY An and PHY Bn.
- B. RXD DTO prevents a single branch-stuck-dominant condition from blocking the redundant branch through the AND logic on RXD. The transceivers signal a received bus stuck dominant fault through the FAULT pin. The system detects which branch is stuck dominant and issues a system warning. Other network faults on a single branch that appear as recessive (not blocking the redundant network) may be detected through diagnostic routines and using the Silent Mode of the PHYs to use only one branch at a time for transmission during diagnostic mode. This combination allows robust fault detection and recovery within single branches so that they may be repaired and again provide redundancy of the physical layer.

Figure 20. Typical Redundant Physical Layer Topology Using the SN65HVD257 Device

10.2.1.3 Application Curves

Figure 21 shows the typical loop delay through the transceiver based on the differential resistive load between CANH and CANL.

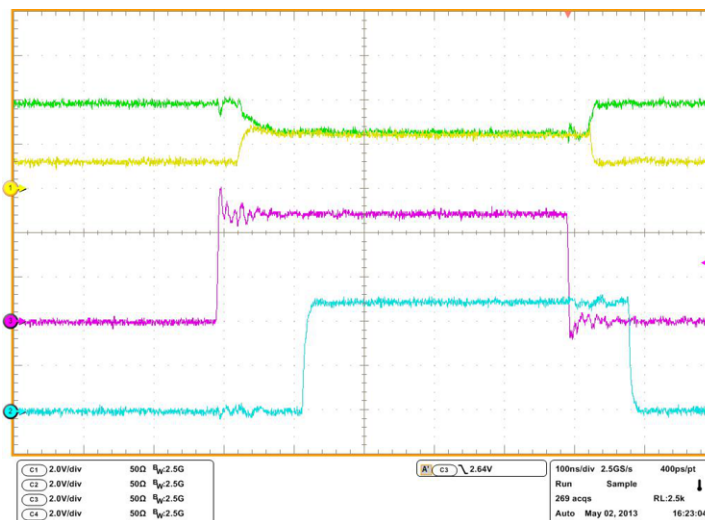


Figure 21. Typical TXD to RXD Loop Delay

Typical Applications (continued)

10.2.2 Typical 3.3-V Microcontroller Application

The SN65HVD256 device has a second supply voltage pin used for level shifting the input and output pins. This can be used for applications where there is a 3.3-V microcontroller and a 5-V CAN transceiver.

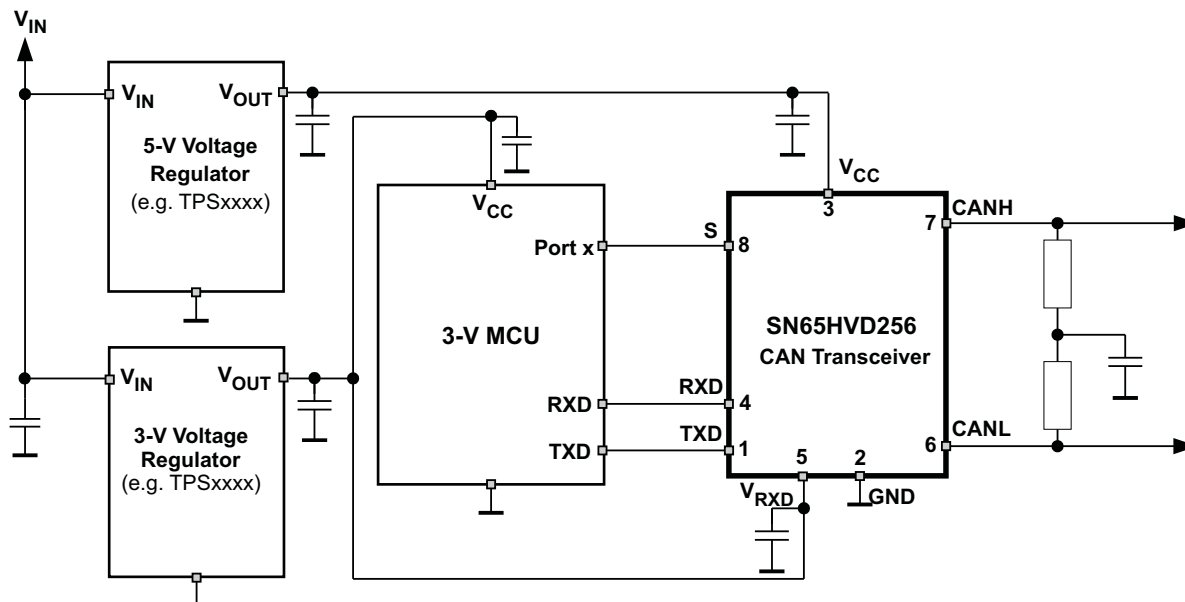


Figure 22. Typical 3.3-V Application

11 Power Supply Recommendations

To ensure reliable operation at all data rates and supply voltages, each supply must be decoupled with a 100-nF ceramic capacitor located as close as possible to the supply pins. The TPS76350 device is a linear voltage regulator suitable for the 5-V supply rail.

12 Layout

12.1 Layout Guidelines

For the PCB design to be successful, start with the design of the protection and filtering circuitry because ESD and EFT transients have a wide frequency bandwidth from approximately 3-MHz to 3-GHz and high frequency layout techniques must be applied during PCB design. On chip IEC ESD protection is good for laboratory and portable equipment but is usually not sufficient for EFT and surge transients occurring in industrial environments. Therefore, robust and reliable bus node design requires the use of external transient protection devices at the bus connectors. Placement at the connector also prevents these harsh transient events from propagating further into the PCB and system.

Use V_{CC} and ground planes to provide low inductance.

NOTE

High frequency current follows the path of least inductance and not the path of least resistance.

Design the bus protection components in the direction of the signal path. Do not force the transient current to divert from the signal path to reach the protection device. Below is a list of layout recommendations when designing a CAN transceiver into an application.

- **Transient Protection on CANH and CANL:** Transient Voltage Suppression (TVS) and capacitors (D1, C5 and C7 shown in [Figure 23](#)) can be used to protect the system level transients like EFT, IEC ESD, and Surge. These devices must be placed as close to the connector as possible. This prevents the transient energy and noise from penetrating into other nets on the board.
- **Bus Termination on CANH and CANL:** [Figure 23](#) shows split termination where the termination is split into two resistors, R5 and R6, with the center or split tap of the termination connected to ground through capacitor C6. Split termination provides common mode filtering for the bus. When termination is placed on the board instead of directly on the bus, care must be taken to ensure the terminating node is not removed from the bus, as this causes signal integrity issues if the bus is not properly terminated on both ends.
- **Decoupling Capacitors on V_{CC} and V_{RXD} :** Bypass and bulk capacitors must be placed as close as possible to the supply pins of transceiver (examples are C2, C3, C5, and C6).
- **Ground and power connections:** Use at least two vias for V_{CC} , V_{IO} , and ground connections of bypass capacitors and protection devices to minimize trace and via inductance.
- **Digital inputs and outputs:** To limit current of digital lines, serial resistors may be used. Examples are R1, R2, R3, R4, and R5.
- **Filtering noise on digital inputs and outputs:** To filter noise on the digital I/O lines, a capacitor may be used close to the input side of the I/O as shown by C1 and C4.
- **External pull-up resistors on input and output pins:** Because the internal pullup and pulldown biasing of the device is weak for floating pins, an external 1-k Ω to 10-k Ω pullup or pulldown resistor must be used to bias the state of the pins during transient events.
- **Fault Output Pin (SN65HVD257 only):** Because the FAULT output pin is an open drain output, an external pullup resistor is required to pull the pin voltage high for normal operation (R5).
- **V_{RXD} Supply (SN65HVD256 only):** The SN65HVD256 device will need additional bypass capacitors for the V_{RXD} supply shown with C5 and C6.
- **TXD input pin:** If an open-drain host processor is used to drive the TXD pin of the device, an external pullup resistor between 1 k Ω and 10 k Ω must be used to help drive the recessive input state of the device (weak internal pullup resistor).

12.2 Layout Example

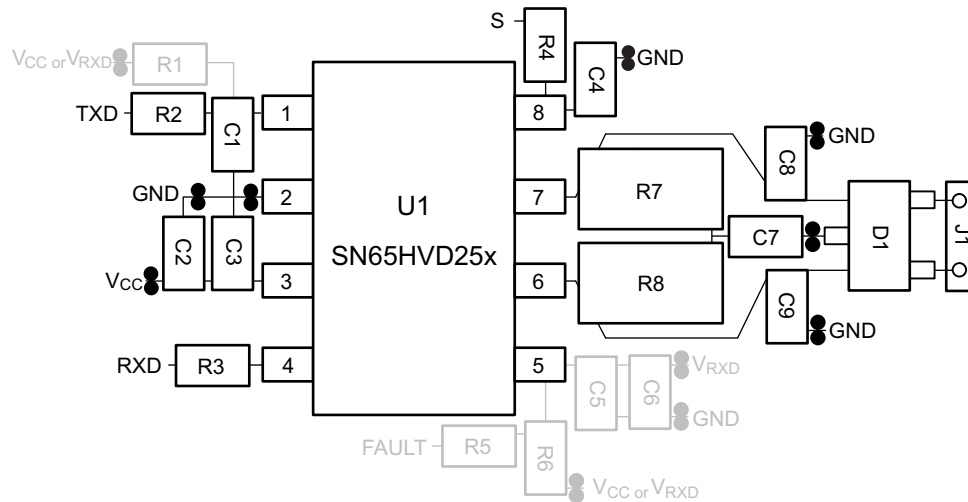


Figure 23. Layout Example

13 器件和文档支持

13.1 相关链接

以下表格列出了快速访问链接。范围包括技术文档、支持与社区资源、工具和软件，并且可以快速访问样片或购买链接。

表 7. 相关链接

器件	产品文件夹	样片与购买	技术文档	工具与软件	支持与社区
SN65HVD255	请单击此处	请单击此处	请单击此处	请单击此处	请单击此处
SN65HVD256	请单击此处	请单击此处	请单击此处	请单击此处	请单击此处
SN65HVD257	请单击此处	请单击此处	请单击此处	请单击此处	请单击此处

13.2 商标

All trademarks are the property of their respective owners.

13.3 静电放电警告



这些装置包含有限的内置 ESD 保护。存储或装卸时，应将导线一起截短或将装置放置于导电泡棉中，以防止 MOS 门极遭受静电损伤。

13.4 术语表

SLYZ022 — TI 术语表。

这份术语表列出并解释术语、首字母缩略词和定义。

14 机械、封装和可订购信息

以下页中包括机械、封装和可订购信息。 这些信息是针对指定器件可提供的最新数据。 这些数据会在无通知且不对本文档进行修订的情况下发生改变。 欲获得该数据表的浏览器版本，请查阅左侧的导航栏。

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
SN65HVD255D	ACTIVE	SOIC	D	8	75	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	HVD255	Samples
SN65HVD255DR	ACTIVE	SOIC	D	8	2500	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	HVD255	Samples
SN65HVD256D	ACTIVE	SOIC	D	8	75	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	HVD256	Samples
SN65HVD256DR	ACTIVE	SOIC	D	8	2500	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	HVD256	Samples
SN65HVD257D	ACTIVE	SOIC	D	8	75	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	HVD257	Samples
SN65HVD257DR	ACTIVE	SOIC	D	8	2500	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	HVD257	Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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TAPE AND REEL INFORMATION



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
SN65HVD255DR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
SN65HVD256DR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
SN65HVD257DR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1

TAPE AND REEL BOX DIMENSIONS



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
SN65HVD255DR	SOIC	D	8	2500	340.5	336.1	25.0
SN65HVD256DR	SOIC	D	8	2500	340.5	338.1	20.6
SN65HVD257DR	SOIC	D	8	2500	340.5	338.1	20.6

TUBE



*All dimensions are nominal

Device	Package Name	Package Type	Pins	SPQ	L (mm)	W (mm)	T (μm)	B (mm)
SN65HVD255D	D	SOIC	8	75	507	8	3940	4.32
SN65HVD256D	D	SOIC	8	75	507	8	3940	4.32
SN65HVD257D	D	SOIC	8	75	507	8	3940	4.32

D0008A**PACKAGE OUTLINE****SOIC - 1.75 mm max height**

SMALL OUTLINE INTEGRATED CIRCUIT



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NOTES:

1. Linear dimensions are in inches [millimeters]. Dimensions in parenthesis are for reference only. Controlling dimensions are in inches. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed .006 [0.15] per side.
4. This dimension does not include interlead flash.
5. Reference JEDEC registration MS-012, variation AA.

D0008A

SOIC - 1.75 mm max height

SMALL OUTLINE INTEGRATED CIRCUIT



LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE:8X



SOLDER MASK DETAILS

4214825/C 02/2019

NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

EXAMPLE STENCIL DESIGN

D0008A

SOIC - 1.75 mm max height

SMALL OUTLINE INTEGRATED CIRCUIT



SOLDER PASTE EXAMPLE
BASED ON .005 INCH [0.125 MM] THICK STENCIL
SCALE:8X

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NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.

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